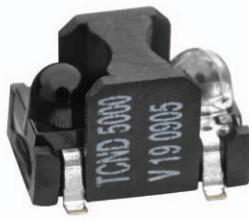
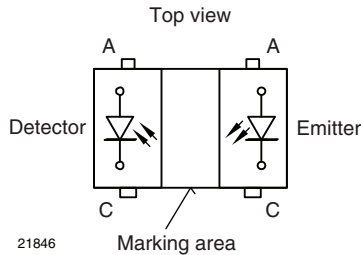


Reflective Optical Sensor with PIN Photodiode Output



19967



21846

DESCRIPTION

The TCND5000 is a reflective sensor that includes an infrared emitter and pin photodiode in a surface mount package which blocks visible light.

FEATURES

- Package type: surface mount
- Detector type: pin photodiode
- Dimensions (L x W x H in mm): 6 x 4.3 x 3.75
- Peak operating distance: 6 mm
- Operating range within > 20 % relative collector current: 2 mm to 25 mm
- Typical output current under test: $I_{ra} > 0.11 \mu\text{A}$
- Daylight blocking filter
- High linearity
- Emitter wavelength: 940 nm
- Lead (Pb)-free soldering released
- Moisture sensitivity level (MSL): 4
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912


RoHS
COMPLIANT

APPLICATIONS

- Proximity sensor
- Object sensor
- Motion sensor
- Touch key

PRODUCT SUMMARY				
PART NUMBER	DISTANCE FOR MAXIMUM CTR_{rel} ⁽¹⁾ (mm)	DISTANCE RANGE FOR RELATIVE $I_{\text{out}} > 20\%$ (mm)	TYPICAL OUTPUT CURRENT UNDER TEST ⁽²⁾ (mA)	DAYLIGHT BLOCKING FILTER INTEGRATED
TCND5000	6	2 to 25	0.0015	Yes

Notes

- (1) CTR: current transfer ratio, $I_{\text{out}}/I_{\text{in}}$
 (2) Conditions like in table basic characteristics/sensors

ORDERING INFORMATION			
ORDERING CODE	PACKAGING	VOLUME	REMARKS
TCND5000	Tape and reel	MOQ: 2000 pcs, 2000 pcs/reel	Drypack

Note

- MOQ: minimum order quantity

ABSOLUTE MAXIMUM RATINGS ($T_{\text{amb}} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
INPUT (EMITTER)				
Reverse voltage		V_R	5	V
Forward current		I_F	100	mA
Peak forward current	$t_p = 50 \mu\text{s}$, $t = 2 \text{ms}$, $T_{\text{amb}} \leq 25\text{ }^{\circ}\text{C}$	I_{FM}	500	mA
Power dissipation		P_V	190	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$



ABSOLUTE MAXIMUM RATINGS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)				
PARAMETER	TEST CONDITION	SYMBOL	VALUE	UNIT
OUTPUT (DETECTOR)				
Reverse voltage		V_R	60	V
Power dissipation		P_V	75	mW
Junction temperature		T_j	100	$^{\circ}\text{C}$
SENSOR				
Ambient temperature range		T_{amb}	-40 to +85	$^{\circ}\text{C}$
Storage temperature range		T_{stg}	-40 to +100	$^{\circ}\text{C}$
Soldering temperature	acc. fig. 14	T_{sd}	260	$^{\circ}\text{C}$

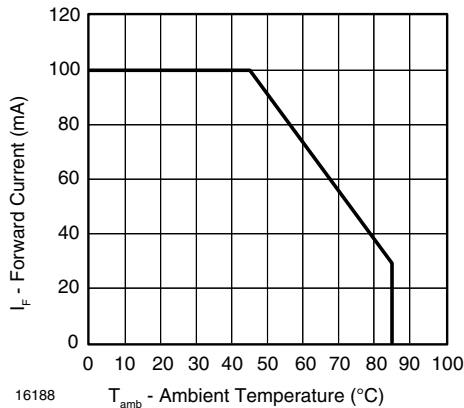


Fig. 1 - Forward Current Limit vs. Ambient Temperature

BASIC CHARACTERISTICS ($T_{amb} = 25\text{ }^{\circ}\text{C}$, unless otherwise specified)						
PARAMETER	TEST CONDITION	SYMBOL	MIN.	TYP.	MAX.	UNIT
INPUT (EMITTER) ⁽¹⁾						
Forward voltage	$I_F = 50\text{ mA}$, $t_p = 20\text{ ms}$	V_F		1.2	1.5	V
Temperature coefficient of V_F	$I_F = 1\text{ mA}$	TK_{V_F}		-1.3		mV/K
Reverse current	$V_R = 5\text{ V}$	I_R			10	μA
Junction capacitance	$V_R = 0\text{ V}$, $f = 1\text{ MHz}$, $E = 0\text{ lx}$	C_j		40		pF
Radiant intensity	$I_F = 20\text{ mA}$, $t_p = 20\text{ ms}$	I_e		11	15	mW/sr
Angle of half intensity		ϕ		± 12		deg
Peak wavelength	$I_F = 100\text{ mA}$	λ_p	930	940		nm
Spectral bandwidth	$I_F = 100\text{ mA}$	$\Delta\lambda$		30		nm
Temperature coefficient of λ_p	$I_F = 100\text{ mA}$	TK_{λ_p}		0.2		nm/K
Rise time	$I_F = 100\text{ mA}$	t_r		15		ns
Fall time	$I_F = 100\text{ mA}$	t_f		15		ns